



# Journal of Semiconductor Technology and Science

## Call Papers for

### September 2005 Special Issue on Semiconductor Devices

Journal of Semiconductor Technology and Science will publish an issue of Semiconductor Devices. It will provide an overview of recent experimental and theoretical progress in the field of Semiconductor Device Physics, Process Technology, and Novel Devices. It is intended to serve as a vehicle for summarizing and highlighting the major developments that have occurred over past few years. The proposed areas will include but are not limited to the following:

#### 1. Device Physics

- ✧ FinFET transistor
- ✧ Metal-insulator transition transistor
- ✧ CNT transistor
- ✧ Memories
- ✧ Nano logic

#### 2. Fabrication process Technologies

- ✧ Nano lithography
- ✧ Nano imprint
- ✧ Self organization
- ✧ Fabrication process for high performance

#### 3. Novel devices

- ✧ 3D storage
- ✧ 3D logic
- ✧ New concept devices

Authors wishing to have their contributions considered for publication in this issue, which will be published in September 2005 issue, are invited to submit an electronic copy of their manuscripts to Editor-in-chief, Kukjin Chun, at no later than **June 30, 2005**. Manuscripts should be submitted in free style double spaced MS Word or pdf file format as an email attachment. See <http://www.jsts.org> for detail. Both regular papers as well as letters are welcome.

In Kyeong Yoo

SAIT

E-mail: [Inyoo@samsung.com](mailto:Inyoo@samsung.com)